

N-channel TrenchMOS standard level FET Rev. 03 — 14 June 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	254	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 175 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 11}}; \\ \text{see } \underline{\text{Figure 12}} \end{array}$		-	-	16	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 11}}; \\ \text{see } \underline{\text{Figure 12}} \end{array}$		-	6.8	8	mΩ



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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \ \Omega; \ V_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 \ ^\circ\text{C}; \ \text{unclamped} \end{split} $	-	-	670	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V _{GS} = 0 V; I _D = 25 A; V _{DS} = 44 V; T _j = 25 °C; see <u>Figure 13</u>	-	35	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7608-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

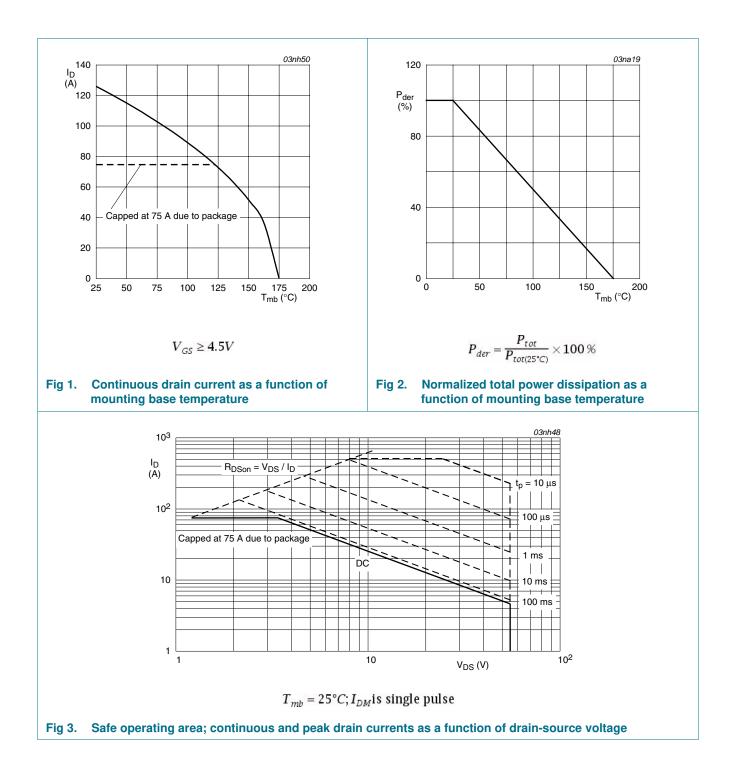
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 1}{\text{Figure } 3}$	<u>[1]</u>	-	-	126	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[2]	-	-	75	А
		T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	75	A
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>		-	-	504	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	254	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drai	n diode						
I _S	source current	T _{mb} = 25 °C	[2]	-	-	75	А
			[1]	-	-	126	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	504	А
Avalanche r	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 75 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} = 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} $		-	-	670	mJ

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

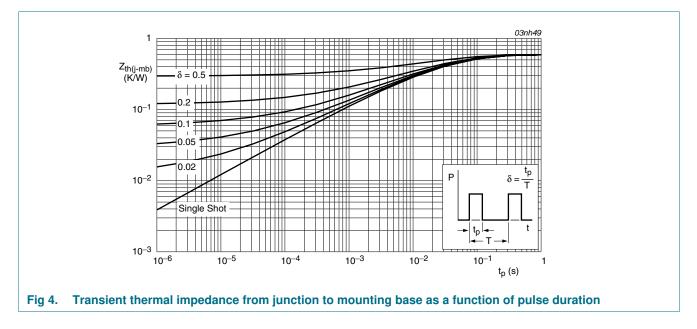
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	0.59	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



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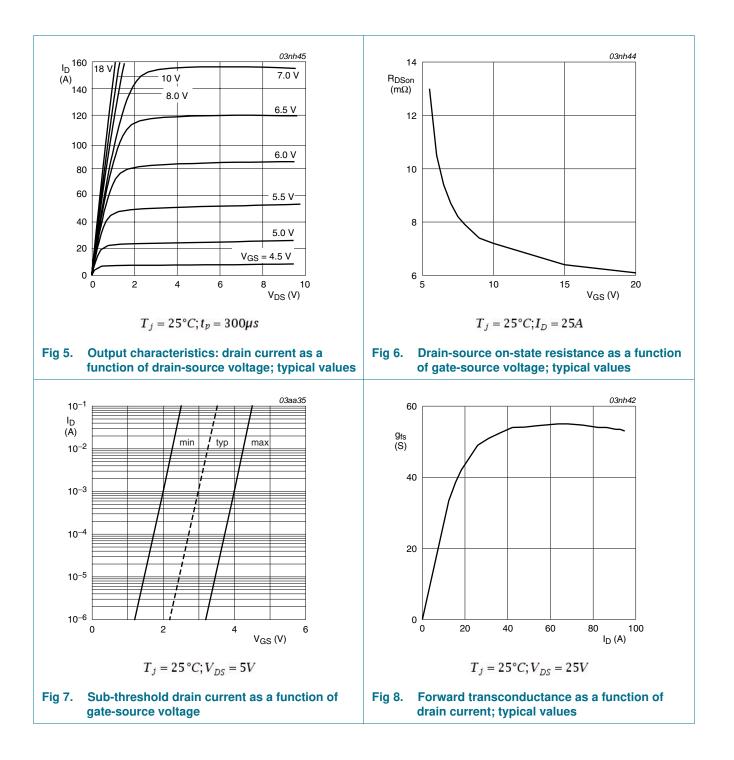
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11;</u> see <u>Figure 12</u>	-	-	16	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	6.8	8	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 0 \text{ V};$	-	76	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } Figure 13$	-	16	-	nC
Q _{GD}	gate-drain charge		-	35	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	3264	4352	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{14}$	-	719	863	pF
C _{rss}	reverse transfer capacitance		-	390	533	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \ V; \ R_L = 1.2 \ \Omega; \ V_{GS} = 5 \ V;$	-	24	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$	-	94	-	ns
t _{d(off)}	turn-off delay time		-	100	-	ns
t _f	fall time		-	80	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 75 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	65	-	ns
Qr	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	170	-	nC

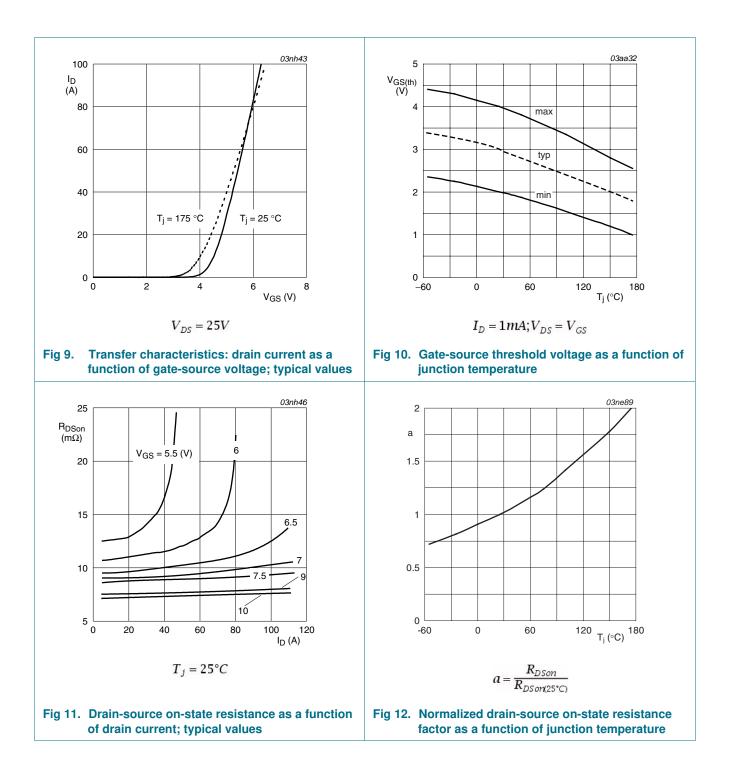
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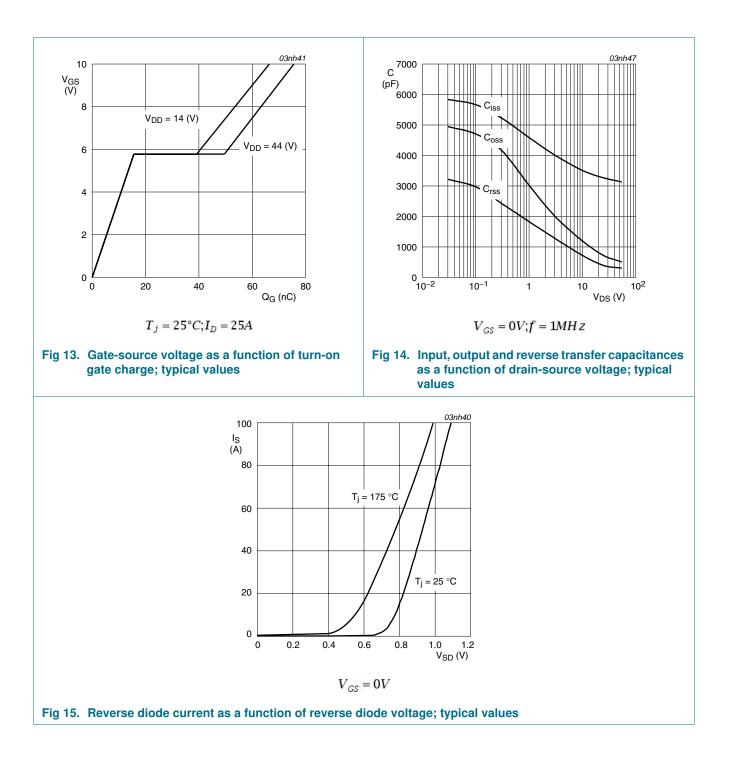
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Package outline 7.

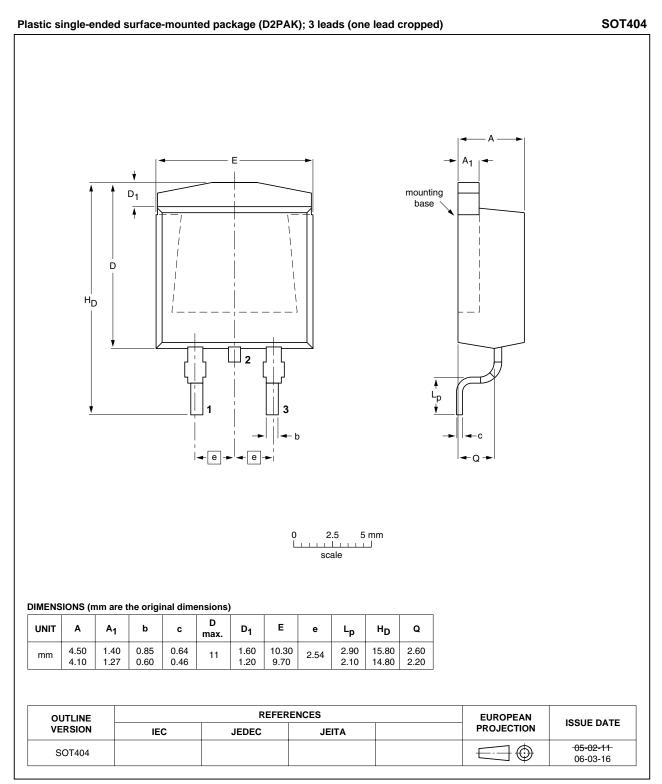


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7608-55A v.3	20100614	Product data sheet	-	BUK7508_7608_55A v.2
Modifications:		of this data sheet has been niconductors.	redesigned to comply with t	the new identity guidelines
	 Legal texts 	have been adapted to the r	new company name where	appropriate.
	 Type number 	er BUK7608-55A separated	from data sheet BUK7508	_7608_55A v.2.
BUK7508_7608_55A v.2	20020117	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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